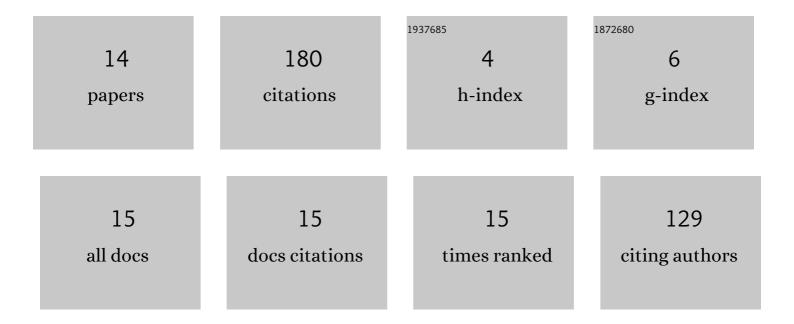
Fabrizio Tamarri

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Activation energy in the early stage of electromigration in Al-1% Si/TiN/Ti bamboo lines. Semiconductor Science and Technology, 1995, 10, 255-259. | 2.0 | 122 |
| 2 | Drawbacks to using NIST electromigration test-structures to test bamboo metal lines. IEEE Transactions on Electron Devices, 1994, 41, 2276-2280. | 3.0 | 18 |
| 3 | Resistance changes due to Cu transport and precipitation during electromigration in submicrometric Al-0.5% Cu lines. Microelectronics Reliability, 1996, 36, 1691-1694. | 1.7 | 13 |
| 4 | Resistance decay after electromigration as the effect of mechanical stress relaxation. Microelectronics Reliability, 1993, 33, 1841-1844. | 1.7 | 9 |
| 5 | Material Properties Measurement and Numerical Simulation for Characterization of Ultra-Low-Power Consumption Hotplates. , 2007, , . | | 4 |
| 6 | Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. Materials Science Forum, 2007, 556-557, 639-642. | 0.3 | 4 |
| 7 | The Evaluation of the True Test Temperature During Wafer-Level Electromigration Tests. Materials Research Society Symposia Proceedings, 1992, 265, 289. | 0.1 | 2 |
| 8 | Fabrication of Pt-Polysilicon Thin-Film Thermopiles: A Preliminary Study. , 0, , . | | 2 |
| 9 | Fully Ion Implanted Vertical p-i-n Diodes on High Purity Semi-Insulating 4H-SiC Wafers. Materials Science Forum, 0, 717-720, 985-988. | 0.3 | 2 |
| 10 | Room Temperature Annealing Effects on Leakage Current of Ion Implanted p ⁺ n 4H-SiC Diodes. Materials Science Forum, 0, 600-603, 1027-1030. | 0.3 | 1 |
| 11 | A comparison among different technological processes for the fabrication of polysilicon-based thermoelectric transducers. , 2006, , . | | Ο |
| 12 | Ion Implanted p ⁺ /n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. Materials Science Forum, 2006, 527-529, 819-822. | 0.3 | 0 |
| 13 | Effects of N Implantation before Gate Oxidation on the Performance of 4H-SiC MOSFET. Materials Science Forum, 0, 615-617, 761-764. | 0.3 | Ο |
| 14 | Micromachined gas calibration sources based on nanometric depth microchannels. Procedia Engineering, 2010, 5, 1344-1347. | 1.2 | 0 |